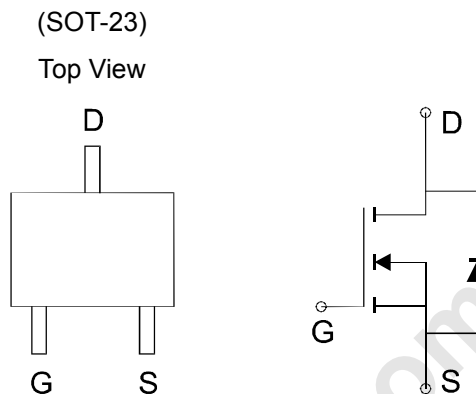


## N-Channel 60V Power MOSFET

### GENERAL DESCRIPTION

The LT2N7002 is the N-Channel enhancement mode field effect transistors are produced using high cell density DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 300mA DC and can deliver pulsed currents up to 1.2A. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

### PIN CONFIGURATION



### FEATURES

- 60V / 0.50A ,  $R_{DS(ON)} = 5.0\Omega @ V_{GS}=10V$
- 60V / 0.30A ,  $R_{DS(ON)} = 5.5\Omega @ V_{GS}=4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

### APPLICATIONS

- High density cell design for low  $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	PARAMETER		Typical	Units
$V_{DSS}$	Drain-Source Voltage		60	V
$V_{GSS}$	Gate-Source Voltage - Continuous		$\pm 20$	V
$V_{GSS}$	Gate-Source Voltage - Non Repetitive ( $t_p < 50\mu s$ )		$\pm 40$	V
$I_D$	Drain Current - Continuous ( $T_J=150^\circ\text{C}$ )	$T_A=25^\circ\text{C}$	300	mA
	- Pulsed (Note 1)		1200	
$P_D$	Power Dissipation	$T_A=25^\circ\text{C}$	350	mW
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 ~ +150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		375	$^\circ\text{C/W}$

Note: 1. Pulse width limited by safe operating area

**N-Channel 60V Power MOSFET**
**Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  Unless Otherwise Specified)

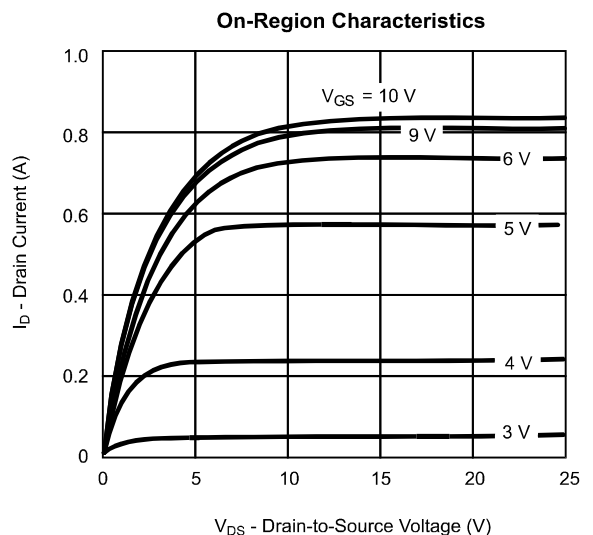
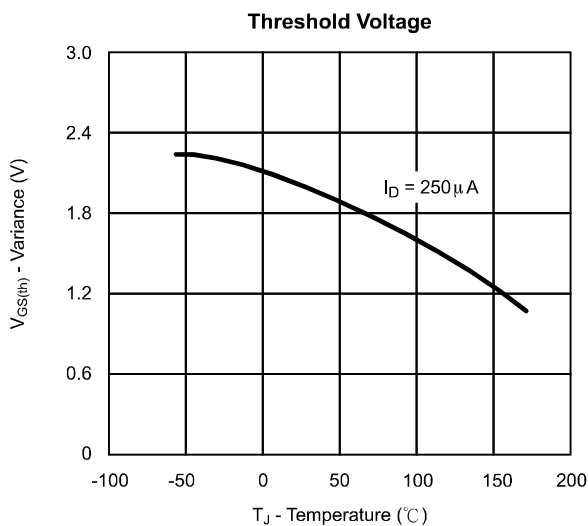
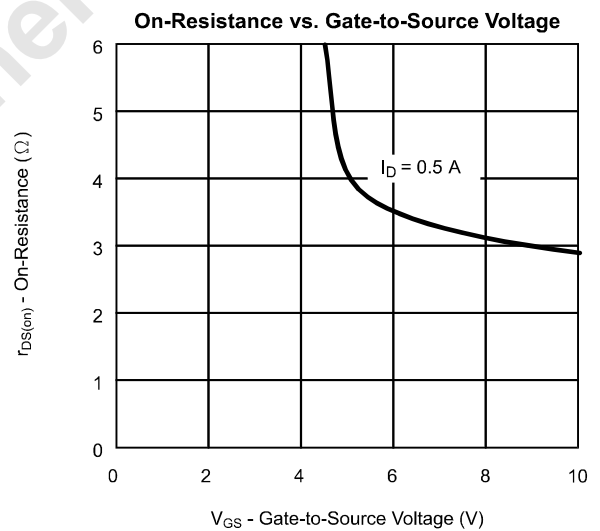
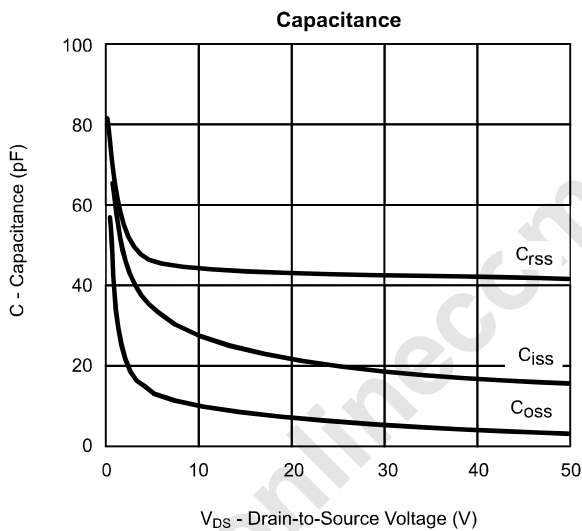
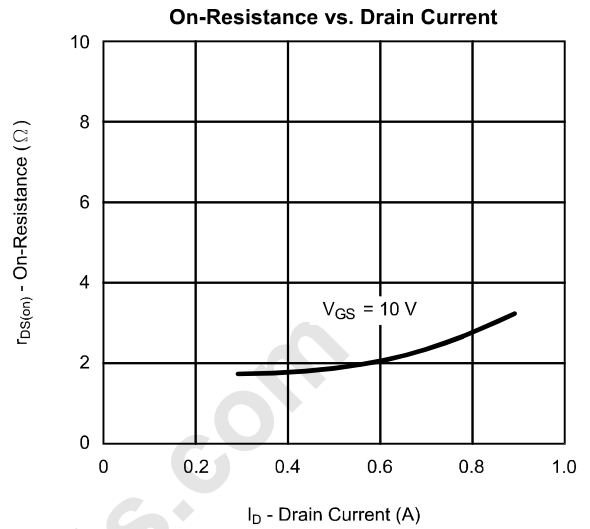
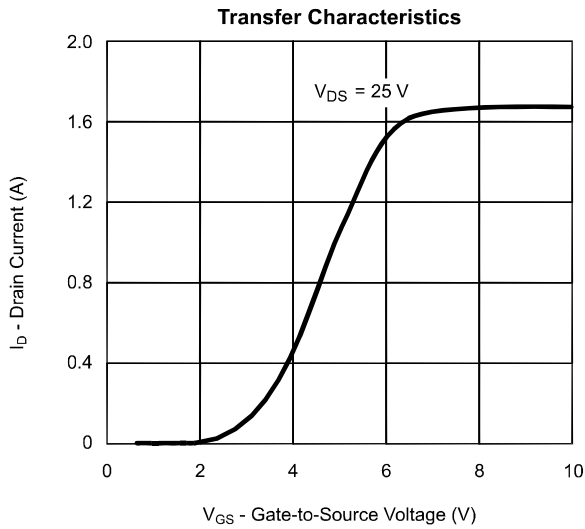
Symbol	Ratings	Test Conditions	Min	Typ	Max	Units
STATIC						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V V <sub>DS</sub> =60V, V <sub>GS</sub> =0V T <sub>J</sub> =125°C	-	-	1 10	μA
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	V <sub>DS</sub> =0V, V <sub>GS</sub> = 20V	-	-	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	V <sub>DS</sub> =0V, V <sub>GS</sub> = -20V	-	-	-100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> =250μA	1	1.7	2.5	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> =500mA V <sub>GS</sub> = 4.5V, I <sub>D</sub> =300mA	-	2.5 3.3	5 5.5	Ω
I <sub>SD</sub>	Source-drain Current		-	-	0.35	A
I <sub>SDM(2)</sub>	Source-drain Current (pulsed)		-	-	1.4	A
G <sub>FS(1)</sub>	Forward Trans-conductance	V <sub>DS</sub> =10V , I <sub>D</sub> =500mA	-	0.6	-	S
V <sub>SD(1)</sub>	Diode Forward Voltage	V <sub>GS</sub> = 0V , I <sub>S</sub> =0.12mA	-	0.85	1.5	V
DYNAMIC						
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V, F=1.0MHz	-	43	-	pF
C <sub>OSS</sub>	Output Capacitance		-	20	-	
C <sub>RSS</sub>	Reverse Transfer Capacitance		-	6	-	
Q <sub>G</sub>	Total Gate Charge	V <sub>DD</sub> =30V, I <sub>D</sub> =1A ,V <sub>GS</sub> = 5V	-	1.4	2.0	nC
Q <sub>GS</sub>	Gate-Source Charge		-	0.8	-	
Q <sub>GD</sub>	Gate-Drain Charge		-	0.5	-	
TD <sub>(ON)</sub>	Turn-On Time	V <sub>DD</sub> =30V,R <sub>G</sub> =4.7Ω, I <sub>D</sub> =500mA V <sub>GS</sub> = 4.5V	-	6	-	nS
T <sub>R</sub>			-	5	-	
TD <sub>(OFF)</sub>	Turn-Off Time		-	15	-	
T <sub>R</sub>			-	6	-	

(1) Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.

(2) Pulse width limited by safe operating area.

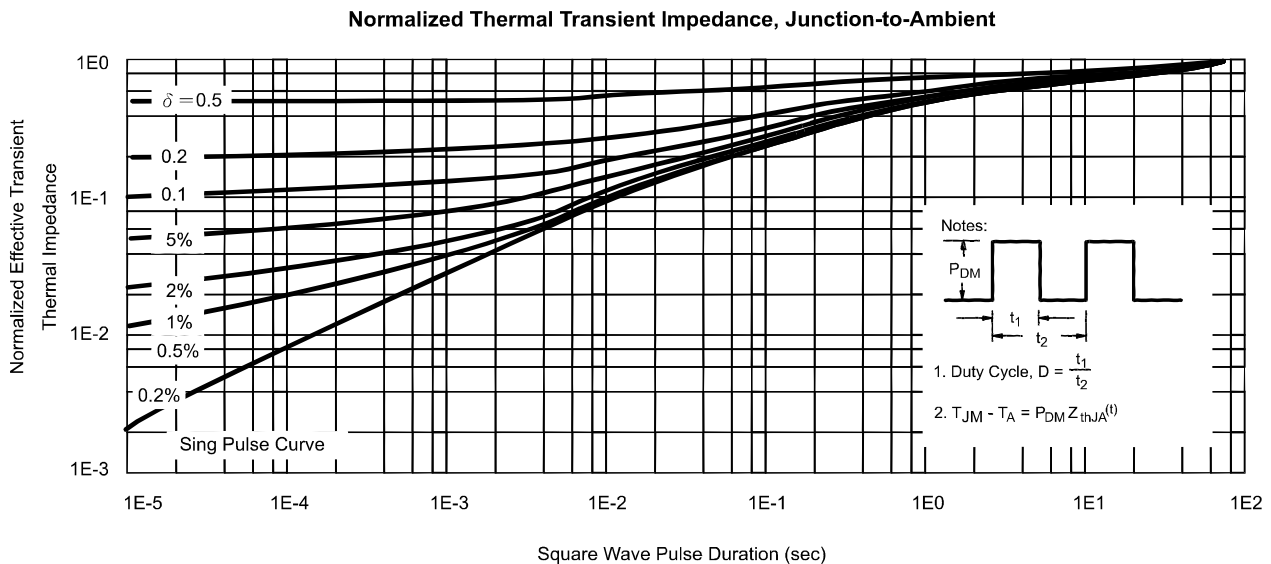
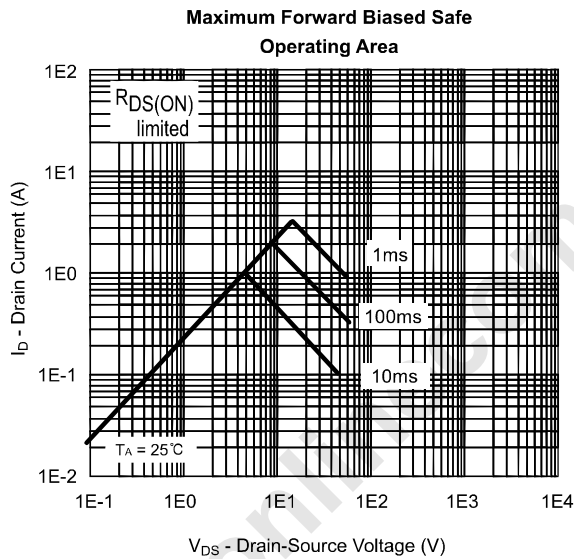
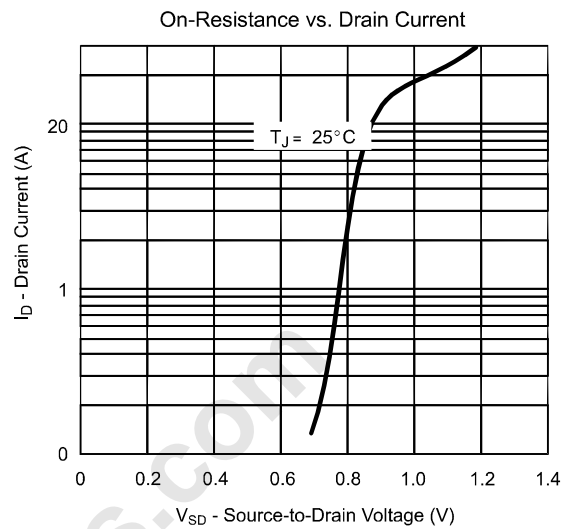
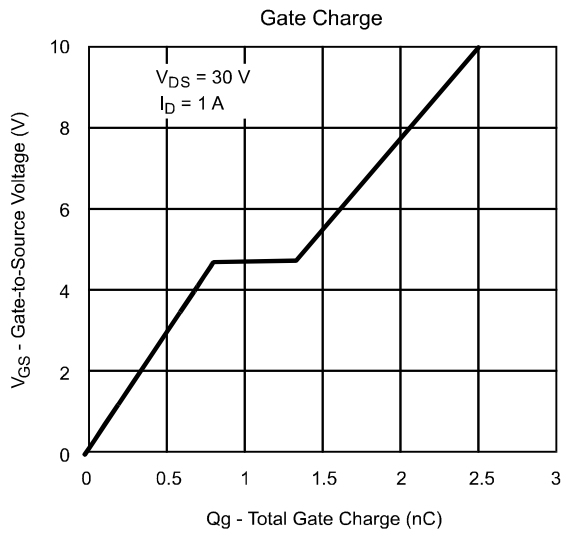
## N-Channel 60V Power MOSFET

### Typical Characteristics (T<sub>J</sub> = 25°C Noted)



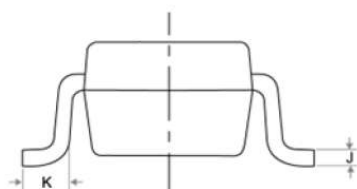
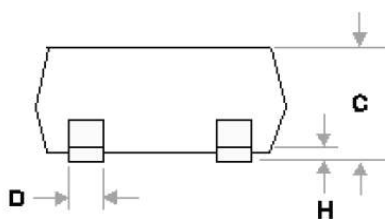
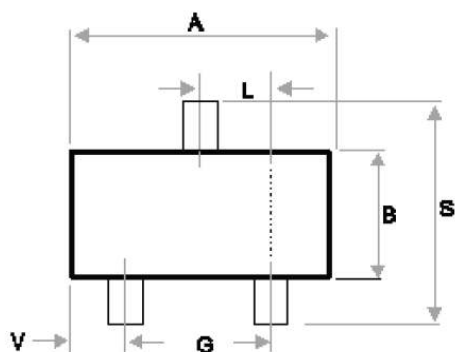
## N-Channel 60V Power MOSFET

### Typical Characteristics (T<sub>J</sub> = 25°C Noted)



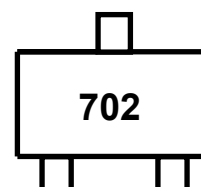
**N-Channel 60V Power MOSFET**

**SOT-23 Package Outline**



DIM	MILLIMETERS (mm)	
	MIN	MAX
A	2.80	3.00
B	1.20	1.70
C	0.90	1.30
D	0.35	0.50
G	1.78	2.04
H	0.010	0.15
J	0.085	0.20
K	0.30	0.65
L	0.89	1.02
S	2.10	3.00
V	0.45	0.60

Body Marking Code:



**N-Channel 60V Power MOSFET****Important Notice and Disclaimer**

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